

--A SEMICONDUCTOR DEVICE HAVING AT LEAST ONE SOURCE/DRAIN REGION FORMED ON AN ISOLATION REGION AND A METHOD OF MANUFACTURE THEREFOR--

IN THE CLAIMS

(1) Kindly rewrite Claim 1 as follows:

SUB B1 >

a¹

1. (Amended) A semiconductor device, comprising:
a semiconductor substrate;
a gate formed above the semiconductor substrate;
an isolation region located within a trench formed in the semiconductor substrate;
at least a portion of one of a source/drain region formed on the isolation region, but not in the semiconductor substrate.

(2) Kindly rewrite Claim 7 as follows:

SUB B3 >

a²

7. (Amended) A semiconductor device, comprising:
a channel region located in a semiconductor substrate;
a trench located adjacent a side of the channel region;
an isolation region located in the trench; and
at least a portion of one of a source/drain region located on the isolation region, but not in the semiconductor substrate.

(3) Kindly rewrite Claim 12 as follows:

SUB B5 >

a³

12. (Amended) A semiconductor device, comprising:

a3
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~~a channel region located in a semiconductor substrate;
an isolation region located adjacent the channel region, the isolation region being located within a trench formed in the semiconductor substrate and not extending under the channel region;
and
source/drain regions having a first portion located in the semiconductor substrate and a second portion located on the isolation region, but not in the semiconductor substrate.~~

(4) Kindly rewrite Claim 17 as follows:

SUB B6 >
a4

~~17. (Amended) A semiconductor device, comprising:
a first transistor located adjacent a second transistor, wherein both the first and second transistors are located over a semiconductor substrate;
an isolation region located between the first and second transistors and within a trench located within the semiconductor substrate; and
source/drain regions associated with each of the first and second transistors, each of the source/drain regions having a first portion located in the semiconductor substrate and a second portion located on the isolation region, but not in the semiconductor substrate.~~

(5) Kindly rewrite Claim 21 as follows:

SUB B7 >
a5

~~21. (Amended) A method of manufacturing a semiconductor device, comprising:
providing a semiconductor substrate;
creating a gate above the semiconductor substrate;
forming an isolation region within a trench located in the semiconductor substrate;~~

forming at least a portion of one of a source/drain region above the isolation region, but not in the semiconductor substrate.

*A5
Concl*
[6] Kindly rewrite Claim 22 as follows:

22. (Amended) The method as recited in Claim 21 wherein forming an isolation region includes forming an isolation region adjacent to the semiconductor substrate.

[7] Kindly rewrite Claim 27 as follows:

SUB B9 >
27. (Amended) An integrated circuit, comprising:

semiconductor devices, including;

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a semiconductor substrate;

a gate formed above the semiconductor substrate;

an isolation region located within a trench formed in the semiconductor substrate;

at least a portion of one of a source/drain region formed above the isolation region,

but not in the semiconductor substrate; and

interconnect structures contacting the semiconductor devices.

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[8] Kindly cancel Claim 33 without prejudice or disclaimer.